Hermetic Infrared Emitting Diode



OP215, OP216

Features:

- Hermetically sealed package
- Mechanically and spectrally matched to other OPTEK devices
- Designed for direct mount to PCBoard
- Enhanced temperature range



Description:

Each **OP215** and **OP216** device is an 890 nm gallium aluminum arsenide infrared emitting diode (GaAlAs), mounted in a hermetically sealed "pig tale" package with an enhanced temperature range and a narrow irradiance pattern that provides high on-axis intensity for excellent coupling efficiency. These devices offer significantly higher power output than GaAs at equivalent drive currents and have a wavelength that is matched to silicon's peak response. Their small package size permits high device density mounting.

The OP216A device provide an additional mounting tab connected to the Cathode/Case.

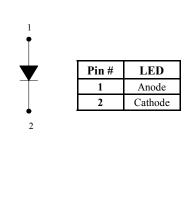
these LEDs are mechanically and spectrally matched to the OP300 series, OP516, OP600 series and OP640 series devices.

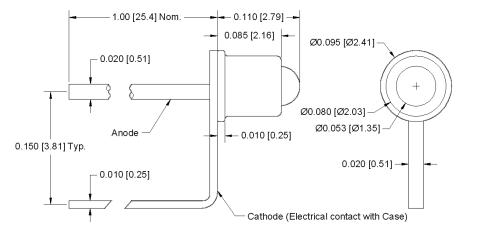
<u>Please refer to Application Bulletins 208 and 210 for additional design information and reliability (degradation) data, and to Application Bulletin 202 for pill-type soldering to PCBoard.</u>

Applications:

- Non-contact reflective object sensor
- Assembly line automation
- · Machine automation
- Machine safety
- End of travel sensor

Ordering Information								
Part	LED Peak	Optical Power mW/						
Number	Wavelength	cm ² (Min)	Angle					
OP215A OP216	A 890 mm	1.20	24°					







General Note

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Electrical Specifications

Absolute Maximum Ratings (T _A = 25° C unless otherwise noted)				
Storage Temperature Range	-65° C to +150° C			
Operating Temperature Range	-65°C to +125°C			
Reverse Voltage	2.0 V			
Continuous Forward Current	100 mA			
Peak Forward Current (2μs pulse with 0.1% duty cycle)	1.0 A			
Lead Soldering Temperature [1/16 inch (1.6 mm) from case for 5 seconds with soldering iron]	260° C ⁽¹⁾⁽²⁾			
Power Dissipation	150 mW ⁽³⁾			

Electrical Characteristics (T _A = 25° C unless otherwise noted)									
SYMBOL	PARAMETER	MIN	ТҮР	MAX	UNITS	TEST CONDITIONS			
Input Diode									
E _{E (APT)} (3)	Apertured Radiant Incidence OP216A	1.20	-	-	mW/cm²	I _F = 50 mA ⁽⁴⁾			
V_{F}	Forward Voltage	-	-	1.80	V	I _F = 50 mA			
I _R	Reverse Current	-	-	100	μΑ	V _R = 2.0 V			
λ_{P}	Wavelength at Peak Emission	-	890	-	nm	I _F = 10 mA			
В	Spectral Bandwidth between Half Power Points	-	80	-	nm	I _F = 10 mA			
Δλ /ΔΤ	Spectral Shift with Temperature	-	+0.18	-	nm/°C	I _F = Constant			
ӨнР	Emission Angle at Half Power Points	-	24	-	Degree	I _F = 50 mA			
t _r	Output Rise Time	-	500	-	ns	I _{F(PK)} =100 mA, PW=10 μs, and D.C.=10.0%			
t _f	Output Fall Time	-	250	-	ns				

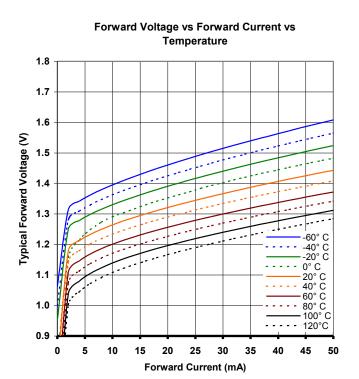
Notes:

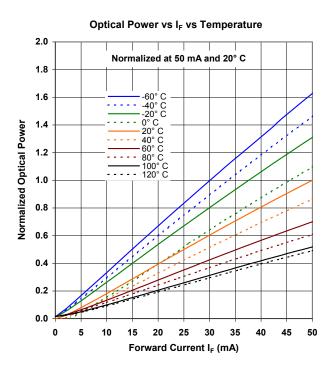
- 1. Refer to Application Bulletin 202 which reviews proper soldering techniques for pill-type devices.
- 2. No clean or low solids. RMA flux is recommended. Duration can be extended to 10 seconds maximum when flow soldering.
- 3. Derate linearly 1.50 mW/° C above 25° C.
- 4. For OP216, E_{E(APT)} is a measurement using a 0.180" (4.57 mm) diameter apertured sensor placed 0.653" (16.59 mm) from the lens tip. E_{E(APT)} is not necessarily uniform within the measured area.

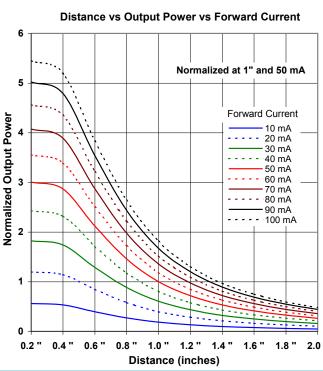
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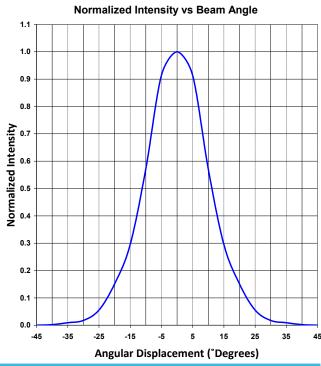


Performance OP215 & OP216









General Note